

* Cuvount-voltage relationship in a PN junction

diode / Diode equation:

 $T_{D} = T_{S} \left(e^{\frac{V_{D}}{NV_{T}}} - 1 \right)$ Shockleys equation
(Diode equation)

where, ID is diode current in mA

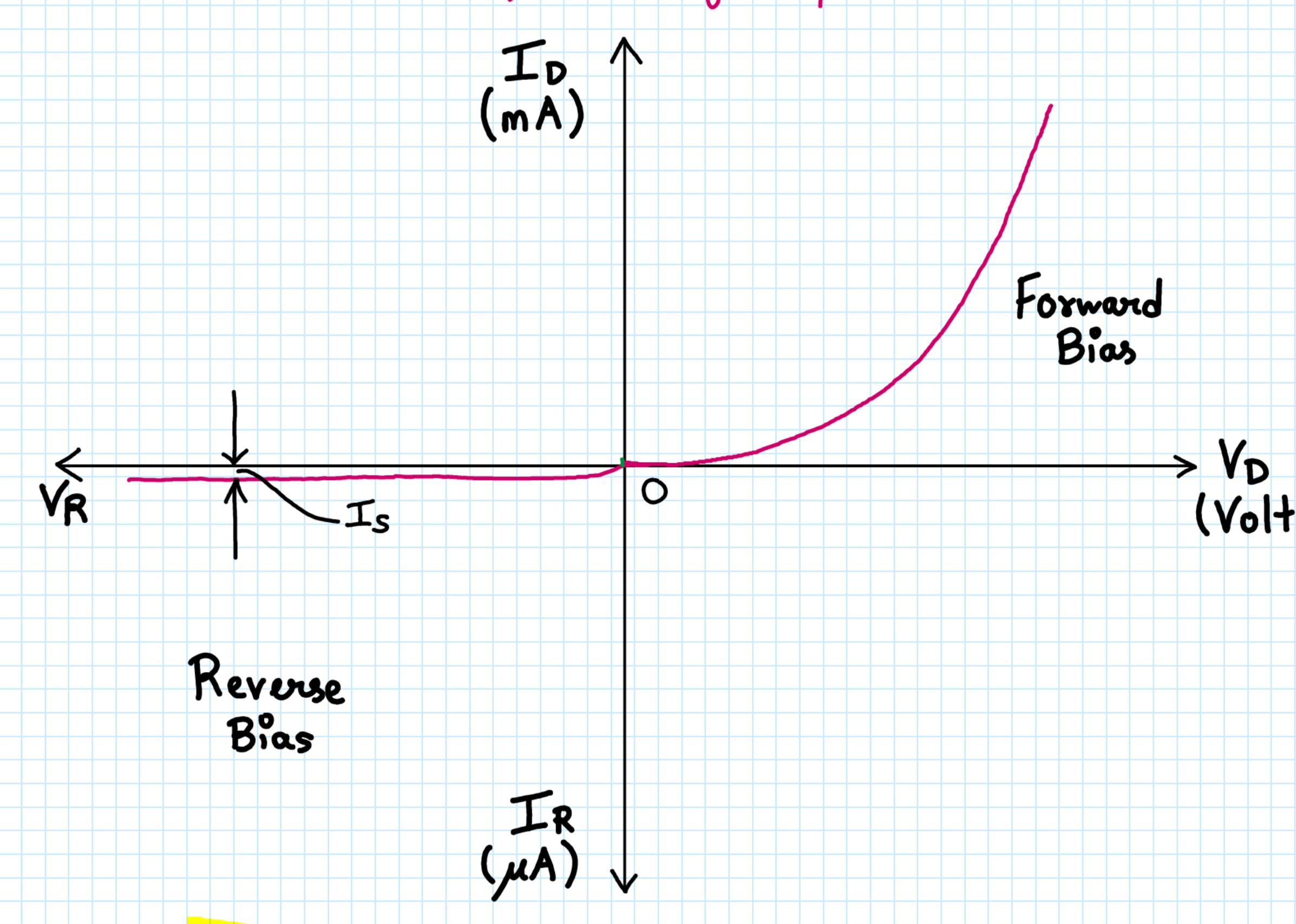
Is is leakage or reverse saturation current in μA or nAn is ideality factor

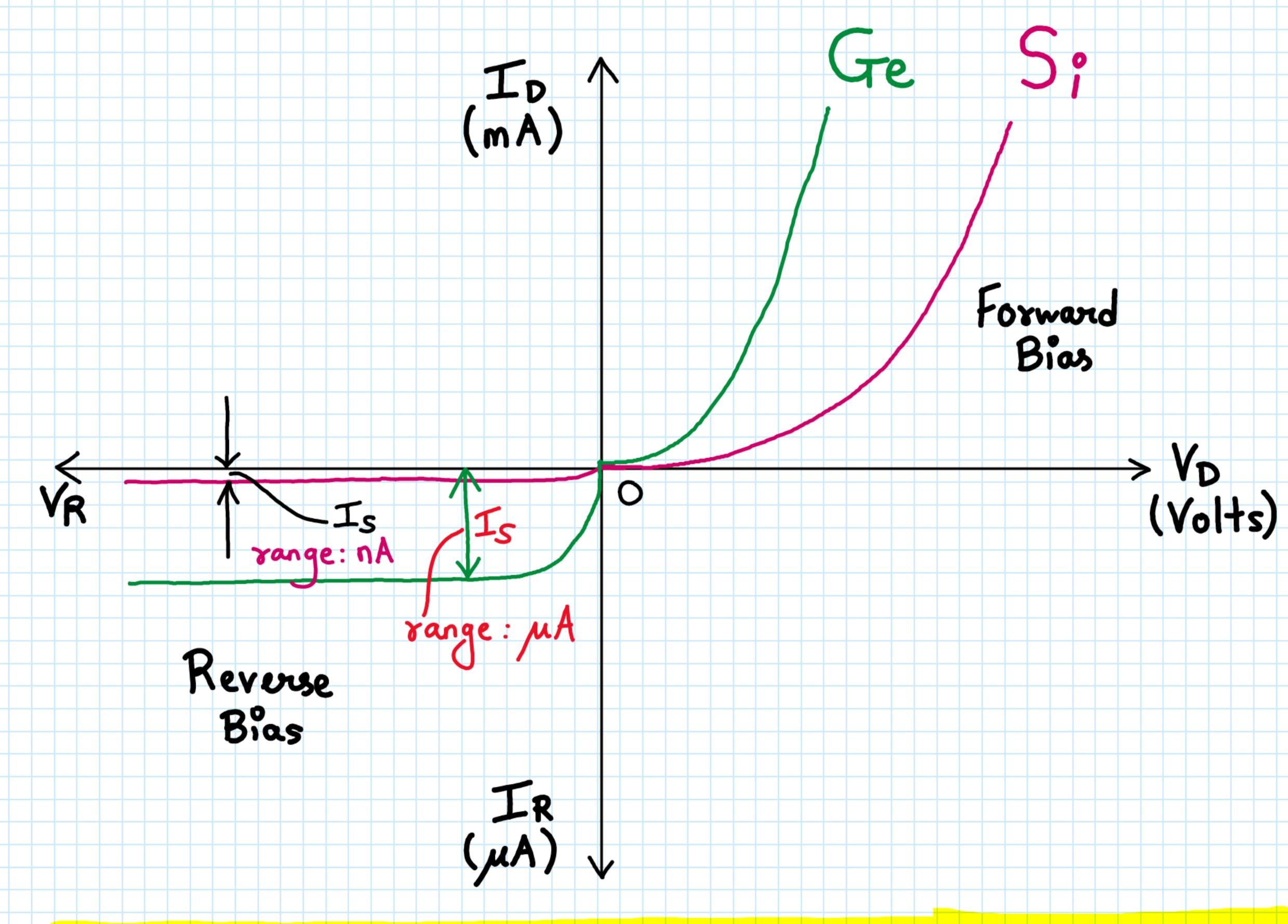
n is I for Ge and n is 2 for Si

V_T is thermal voltage at T = 300K (27°C)

 $V_T = \frac{KT}{2} = \frac{T}{11600}$; $V_T = 26 \text{ mV}$ at T = 300 K

Vr is also volt equivalent of temperature





* Observations (from I-V characteristics)

- 1) Diode equation tells us how current ID flows for given amount of applied voltage VD
- 2) In forward bias, ID increases exponentially with applied forward voltage VD as per diode equation

$$T_D = T_S \left(e^{\frac{V_D}{\eta_V V_T}} - 1 \right)$$

Diode is forward biased if VD positive (Anode is positive

3) In reverse bias, VD is negative (large value), thus

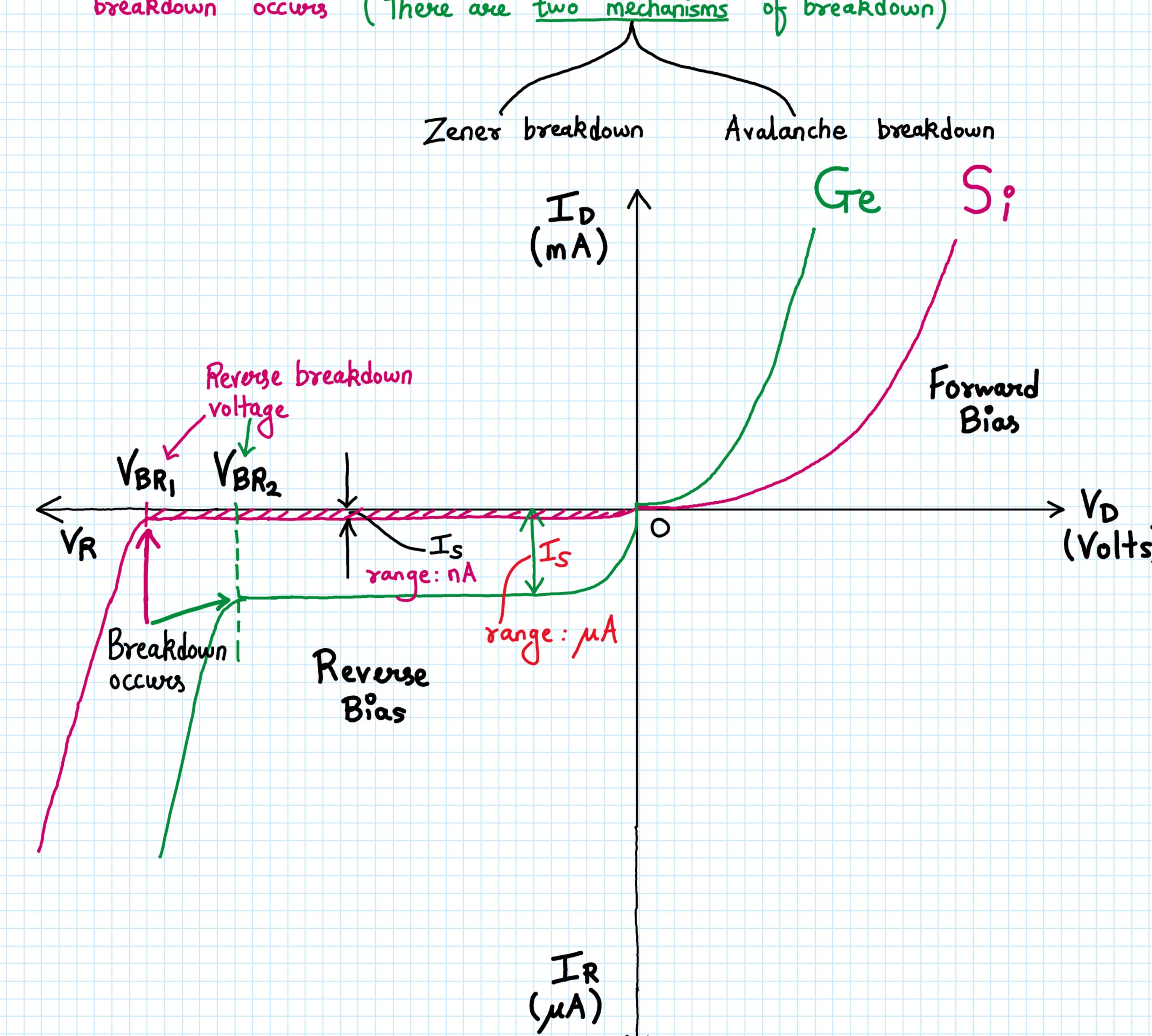
 $I_D = -I_S$ in reverse bias

This means that the reverse current in a diode is constant and it is equal to Is ile reverse convent saturates to Is in the reverse direction (hence the name reverse saturation current)

4) In reverse bias, ID is independent of applied reverse bias (A positive value of ID means that current flows from pside to n-side)

* Real diodes: Zener & Avalanche

- 1) As observed in reverse bias prijunction conduct very small current (in mA or nA) & it is constant
- 2) It is true, until a ocitical reverse voltage is reached & junction breakdown occurs (There are two mechanisms of breakdown)



- 3) When reverse-bias voltage VBR, (say 50v) for Si diodes, then the reverse current in the diode increases rapidly
- (4) When breakdown occurs, the voltage across the diode terminals remains almost more or less constant